

1. (a) A CMOS inverter pair is shown in Fig. 1(a). Let  $V_{TN}=0.8V$ ,  $V_{TP}=-0.8V$ , and  $K_n=K_p$ .  
 (i) If  $v_{O1}=0.6V$ , determine  $v_1$  and  $v_{O2}$ . (ii) Determine the range of  $v_{O2}$  for which both  $N_2$  and  $P_2$  are biased in the saturation region. (20%)
- (b) What is the function realized at Y in the CMOS circuit shown in Fig. 1(b)? (5%)

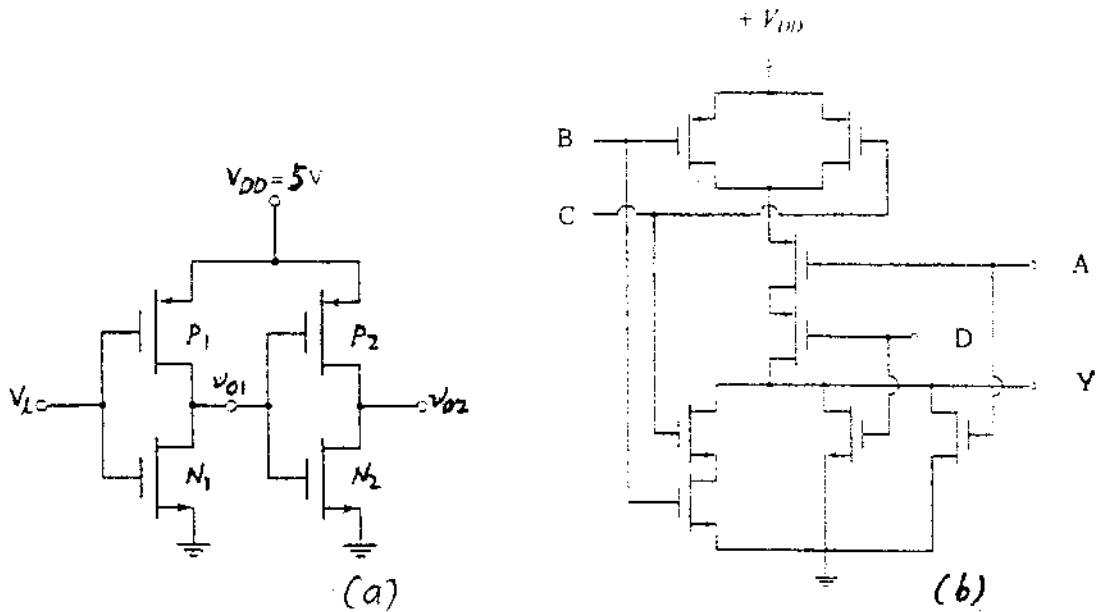


Fig. 1

2. Your answers must be as brief as possible for the following questions
  - (a) List the parameters used to specify the transmission characteristics of a low-pass filter. (5%)
  - (b) A filter transfer function is written as the ratio of two polynomials. The degree of its denominator is P and the degree of its numerator is R. What's the order of the filter? (5%)
  - (b) For the filter in (b) to be stable, what is the relation between P and Q. (5%)
  - (c) For the amplifier in Fig. 2, what's the class of its output stage? (Hint: Maybe one of class AB, A, B, C, D, E, ..., etc.) (5%)
  - (d) What is the function of the R and Cc in Fig. 2? (5%)
3. A multiple amplifier having a first pole at 1MHz and an open-loop gain of 100dB is to be compensated for closed-loop gains as low as 20 dB by introduction of a new dominant pole. At what frequency must the new pole be placed?(3%)
4. Consider the complementary BJT class B output stage and neglect the effects of  $V_{BE}$  and  $V_{CEsat}$ . For  $\pm 10V$  power supplies and a 100- $\Omega$  load resistance, what is the

(背面仍有題目,請繼續作答)

maximum sine-wave output power available? What supply power corresponds? What is the power-conversion efficiency? For output signals of half this amplitude, find the power-conversion efficiency.(10%)

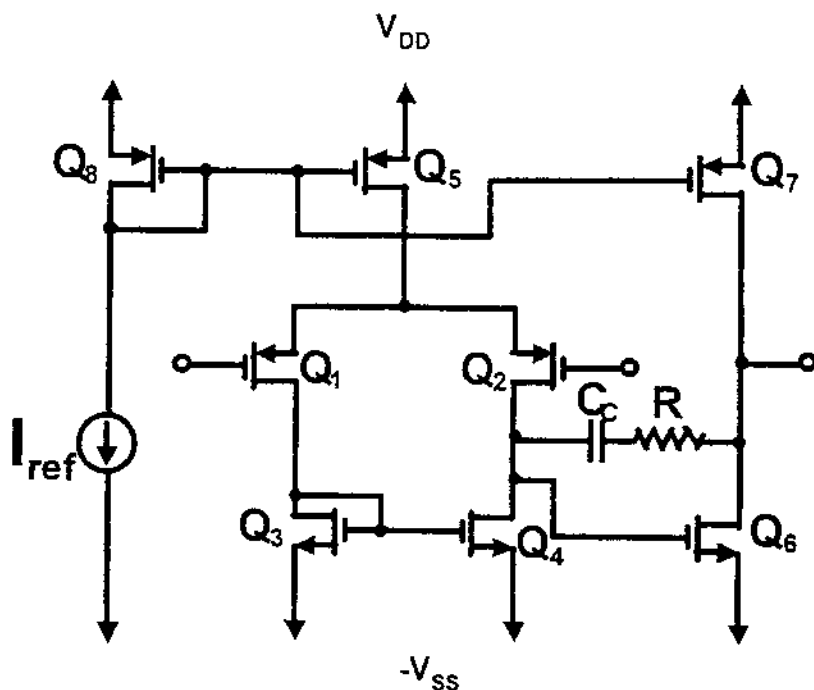


Fig2

5. As the circuit shown in Fig.3, let  $\beta=100$ ,  $C_{\mu}=2\text{pF}$  and  $f_T=400\text{MHz}$ . Calculate the midband gain and the upper 3-dB frequency. (12%)
6. Draw and explain briefly the possible load line of an enhancement-mode n-MOSFET using (a) a forward-biased diode, or (b) a reverse-biased diode, or (c) a depletion-mode n-MOSFET with  $V_{GS} = 0\text{V}$  as the load device. (15%)
7. Calculate the small-signal input resistance  $R_i$  as shown in Fig. 4. Assume  $R_B = R_C = 2\text{ k}\Omega$ ,  $g_m = 25\text{ mS}$ ,  $\beta=100$ , and  $r_o = \infty$ . (10%)

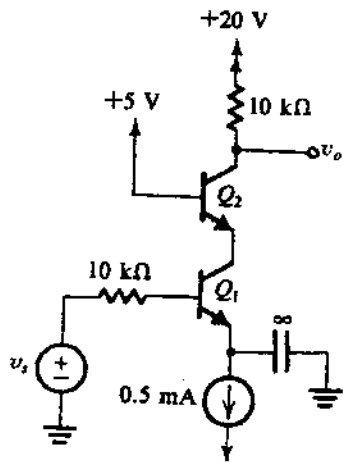


Fig.3

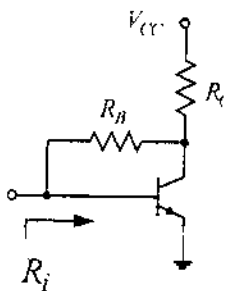


Fig.4